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Substitute for form 1449A/PTO				Application Number Filing Date		GIOIP	-	
SUPP	LEMENTAL INFO	RMA	TION	First Named Inventor	Singh, et al.	JUN 1 7 20	<u> 6</u>	I
DISCLOSURE STATEMENT BY APPLICANT  (Use as many sheets as necessary)			T BY	Group Art Unit	1762	E C	, u	I
				Examiner Name	Unknown	Par San	<b>S</b>	
			j	Attorney Docket Number	AMAT/7729/TCG/EPI/RA			
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	-		U.S. PATENT	DOCUMENTS		
Examiner Initials*	Cite	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	No.'	Number-Kind Code <sup>2 (0 traver)</sup>				
	A1	US-6821825 B2	11/23/2004	Todd		
	A2	US-6797558 B2	09/28/2004	Nuttall, et al.		
	A3	US-6562720 B2	05/13/2003	Thilderkvist, et al.		
	A4	US-6489241 B1	12/03/2002	Thilderkvist, et al.		
	A5	US-6451119 B2	09/17/2002	Sneh, et al.		
	A6	US-6335280 B1	01/01/2002	van der Jeugd		
	A7	US-6291319 B1	09/18/2001	Yu, et al.		
	A8	US-6159852	12/12/2000	Nuttali, et al.		
	A9	US-6042654	03/28/2000	Comita, et al.		
	A10	US-5906680	05/25/1999	Meyerson		
	A11	US-5273930	12/28/1993	Steele, et al.		
	A12	US-5112439	05/12/1992	Reisman, et al.		
	A13	US-20050079691 A1	04/14/2005	Kim, et al.		
	A14	US-20040253776 A1	12/16/2004	Hoffmann, et al.		
	A15	US-20040226911 A1	11/18/2004	Dutton, et al.		
	A16	US-20040033674 A1	02/19/2004	Todd		
	A17	US-20030189208 A1	10/09/2003	Law, et al.		
	A18	US-20020197831 A1	12/26/2002	Todd, et al.		
	A19	US-20020145168 A1	10/10/2002	Bojarczuk, Jr., et al.		
	A20	US-20020090818 A1	07/11/2002	Thilderkvist, et al.		

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²		
	C1	Kamins, et al. "Kinetics of selective epitaxial deposition of Si <sub>1-x</sub> Ge <sub>x</sub> ", Applied Physics Letters, American Institute pf Physics. New York, US, vol. 61, no. 6, 10 August 1992, pp. 689-871			
	C2	Menon, et al. "Loading effect in SiGe layers grown by dichlorosilane- and silane-based epitaxy", Journal of Applied Physics, American Institute of Physics. New York, US, vol. 90, no. 9, 1 November 2001, pp. 4805-4809			

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Inder the Panerwork Reduction Act of 1995, no nections are remained to respo 10/688,426 Application Number Substitute for form 1449A/PTO Filing Date October 17, 2003 Singh, et al. SUPPLEMENTAL INFORMATION First Named Inventor **DISCLOSURE STATEMENT BY** Group Art Unit 1762 **APPLICANT** Unknown **Examiner Name** AMAT/7729/TCG/EPI/RKK Attorney Docket Number (Use as many sheets as necessary) 18 Sheet 2 of 2 **Submission Date** 

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	C3	Sedgwick, et al. "Selective SiGe and heavily As doped Si deposited at low temperature by atmospheric pressure chemical vapor deposition", Journal of Vacuum Science and Technology: Part B, American Institute of Physics. New York, US, vol. 11, no. 3, 1 May 1993, pp. 1124-1128	7	
	C4	Uchino, et al. "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1 µm CMOS ULSIs", Electron Devices Meeting, 1997. Technical Digest, International Washington, DC, USA 7-10 Dec. 1991, New York, NY, USA, IEEE, US, 7 December 1997, pp. 479-482		
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